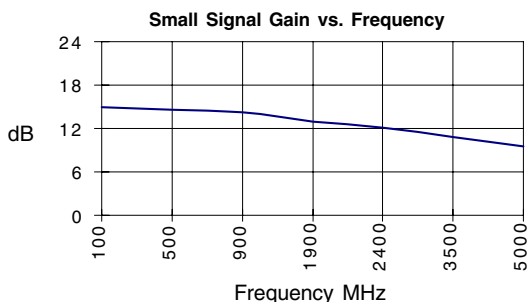


Product Description

Stanford Microdevices' SGA-3286 is a high performance cascadeable 50-ohm amplifier designed for operation at voltages as low as 2.7V. This RFIC uses the latest Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process featuring 1 micron emitters with f_T up to 65 GHz.

This circuit uses a darlington pair topology with resistive feedback for broadband performance as well as stability over its entire temperature range. Internally matched to 50 ohm impedance, the SGA-3286 requires only DC blocking and bypass capacitors for external components.



Preliminary

SGA-3286

DC-3600 MHz Silicon Germanium HBT Cascadeable Gain Block



Product Features

- DC-3600 MHz Operation
- Single Voltage Supply
- High Output Intercept: +25.5dBm typ. at 850 MHz
- Low Current Draw: 35mA at 2.7V typ.
- Low Noise Figure: 3.7dB typ. at 850 MHz

Applications

- Oscillator Amplifiers
- Cordless Phones
- IF/RF Buffer Amplifier
- Drivers for CATV Amplifiers

Symbol	Parameters: Test Conditions: $Z_0 = 50 \text{ Ohms}$, $I_d = 35 \text{ mA}$, $T = 25^\circ\text{C}$		Units	Min.	Typ.	Max.
P_{1dB}	Output Power at 1dB Compression	$f = 850 \text{ MHz}$ $f = 1950 \text{ MHz}$	dBm dBm		12.2 11.3	
S_{21}	Small Signal Gain	$f = \text{DC} - 1000 \text{ MHz}$ $f = 1000 - 2000 \text{ MHz}$ $f = 2000 - 3600 \text{ MHz}$	dB dB dB	13.0	14.3 12.9 10.0	
S_{12}	Reverse Isolation	$f = \text{DC} - 3600 \text{ MHz}$	dB		18.9	
S_{11}	Input VSWR	$f = \text{DC} - 2000 \text{ MHz}$ $f = 2000 - 3600 \text{ MHz}$	-		1.30:1 1.67:1	
S_{22}	Output VSWR	$f = \text{DC} - 3600 \text{ MHz}$	-		1.17:1	
IP_3	Third Order Intercept Point	$f = 850 \text{ MHz}$ $f = 1950 \text{ MHz}$	dBm dBm		25.5 24.8	
NF	Noise Figure	$f = \text{DC} - 1000 \text{ MHz}$ $f = 1000 - 2400 \text{ MHz}$	dB dB		3.7 4.3	
T_D	Group Delay	$f = 1000 \text{ MHz}$	pS		119.0	
V_D	Device Voltage		V	2.4	2.7	3.0

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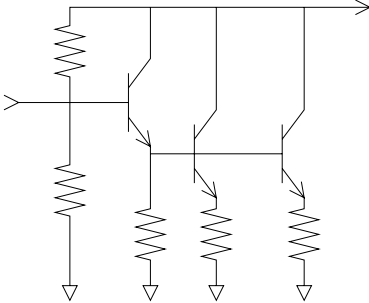
522 Almanor Ave., Sunnyvale, CA 94086

Phone: (800) SMI-MMIC

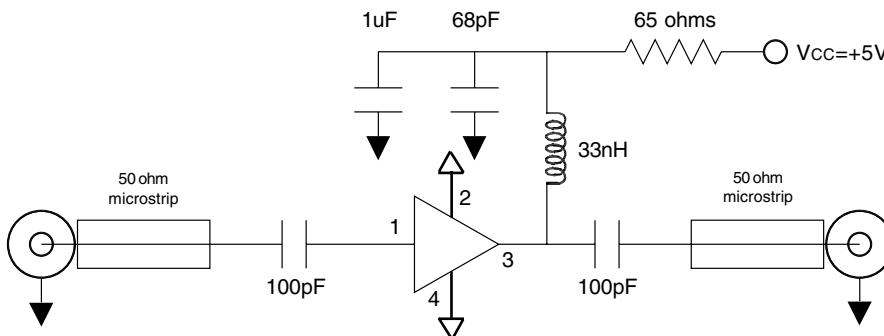
<http://www.stanfordmicro.com>

EDS-100631 Rev A

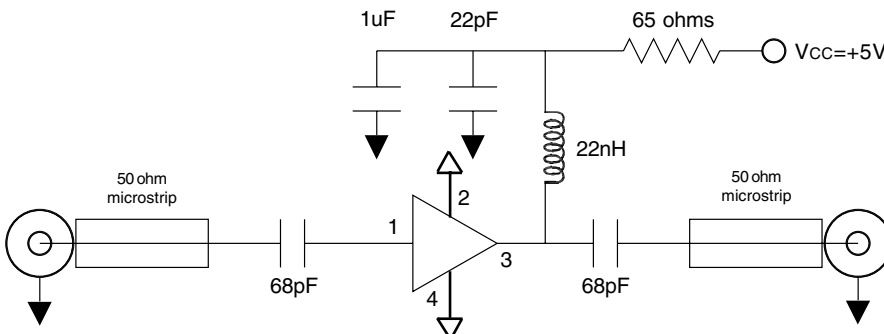
Parameter	Specification			Unit	Test Condition
	Min	Typ.	Max.		
Device Bias					T= 25C
Operating Voltage		2.7		V	
Operating Current		35.0		mA	
500 MHz					T= 25C
Gain		14.6		dB	
Noise Figure		3.7		dB	
Output IP3		25.1		dBm	
Output P1dB		11.8		dBm	
Input Return Loss		22.0		dB	
Isolation		18.4		dB	
850 MHz					T= 25C
Gain		14.3		dB	
Noise Figure		3.7		dB	
Output IP3		25.5		dBm	
Output P1dB		12.2		dBm	
Input Return Loss		18.9		dB	
Isolation		18.5		dB	
1950 MHz					T= 25C
Gain		12.9		dB	
Noise Figure		4.2		dB	
Output IP3		24.8		dBm	
Output P1dB		11.3		dBm	
Input Return Loss		18.4		dB	
Isolation		18.9		dB	
2400 MHz					T= 25C
Gain		12.2		dB	
Noise Figure		4.3		dB	
Output IP3		24.5		dBm	
Output P1dB		10.9		dBm	
Input Return Loss		17.8		dB	
Isolation		19.0		dB	

Pin #	Function	Description	Device Schematic
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
2	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.	
3	RF OUT/ BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.	
4	GND	Sames as Pin 2	

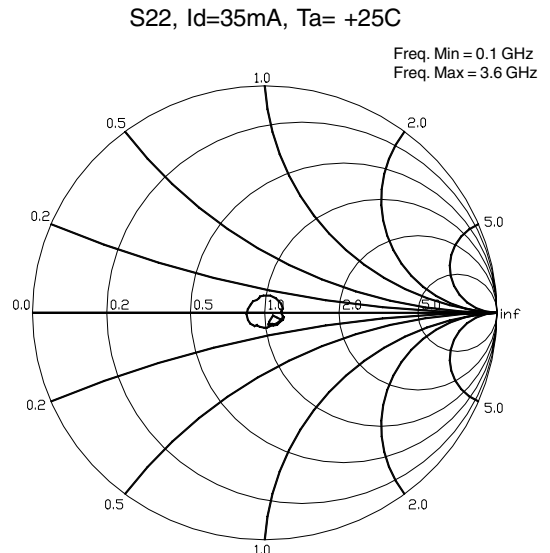
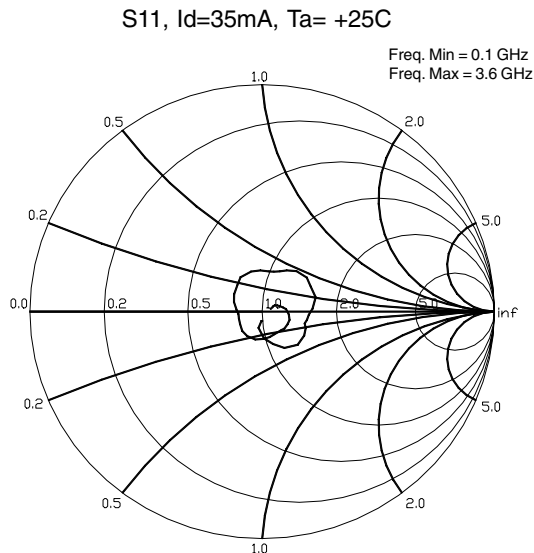
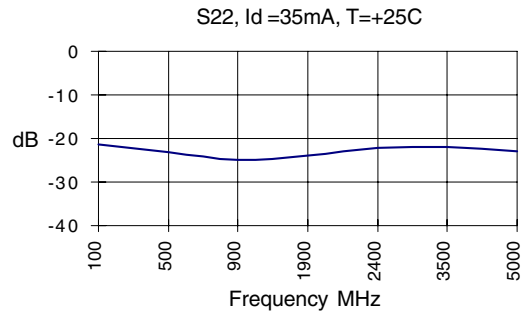
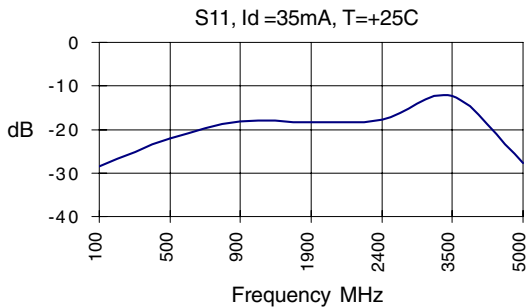
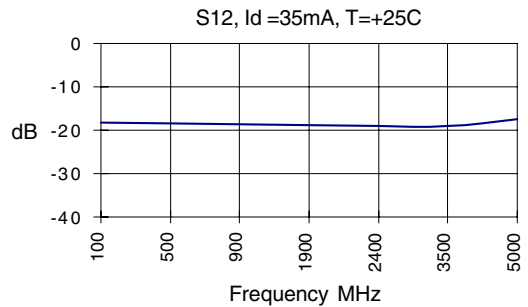
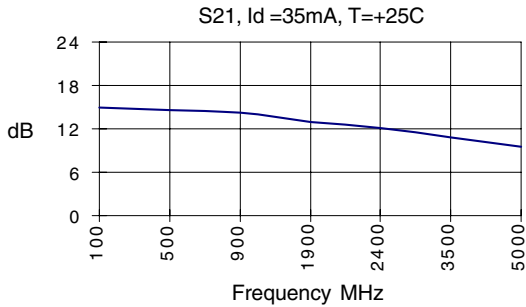
Application Schematic for +5V Operation at 900 MHz



Application Schematic for +5V Operation at 1900 MHz

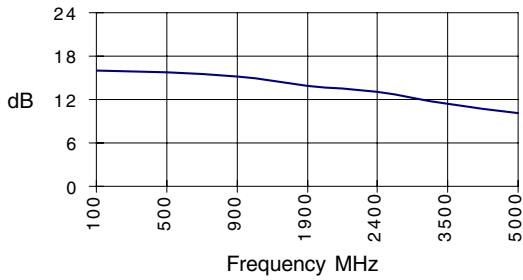


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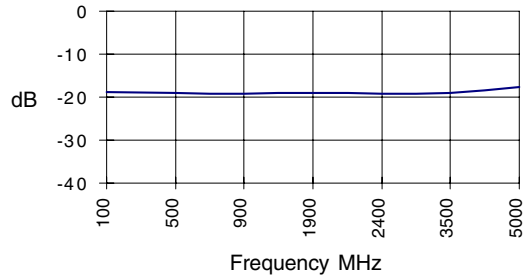


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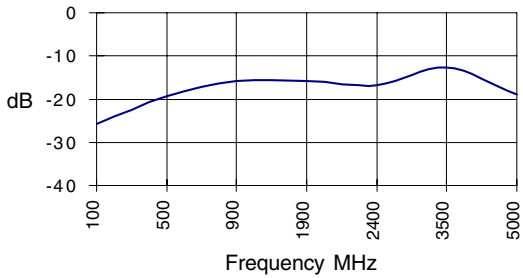
S21, Id =35mA, T=-40C



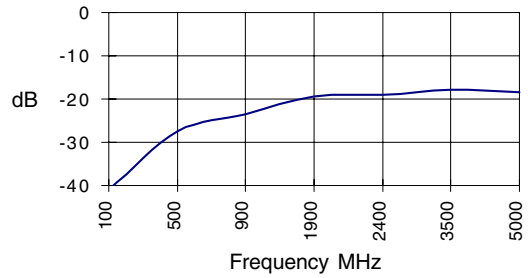
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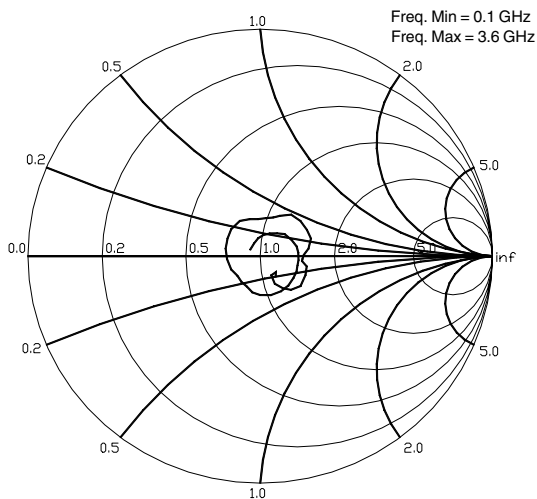
S11, Id =35mA, T=-40C



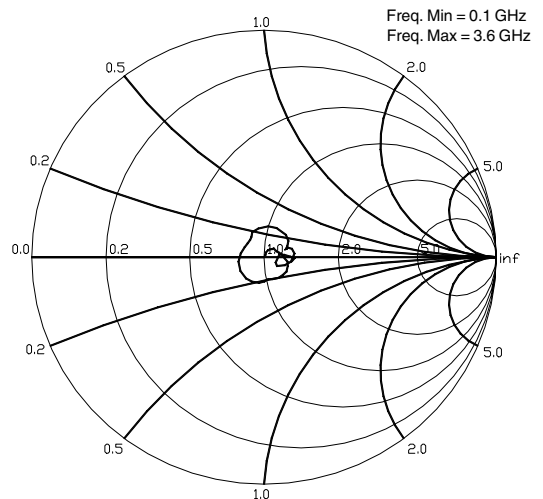
S22, Id =35mA, T=-40C



S11, Id=35mA, Ta= -40C

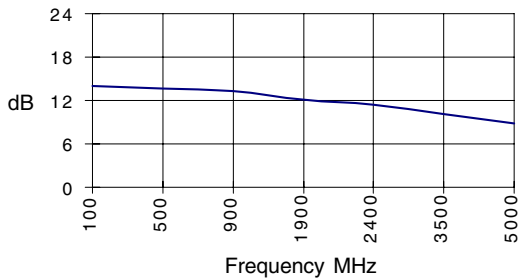


S22, Id=35mA, Ta= -40C

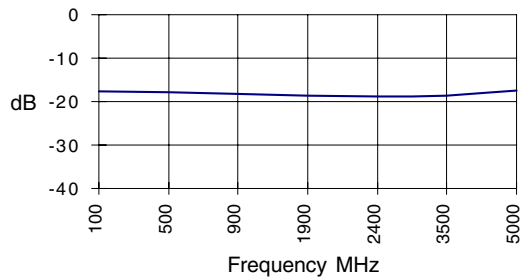


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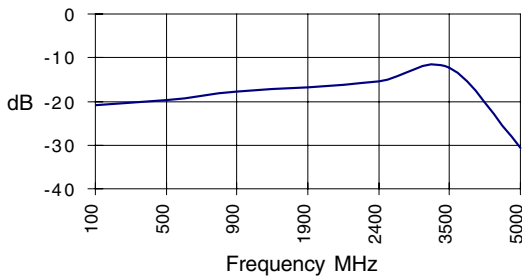
S21, Id =35mA, T=85C



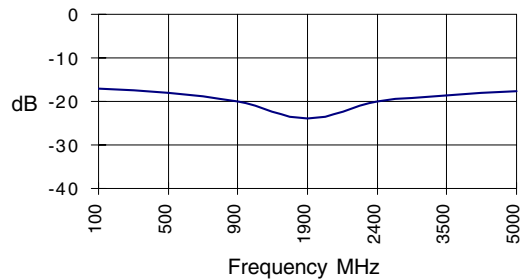
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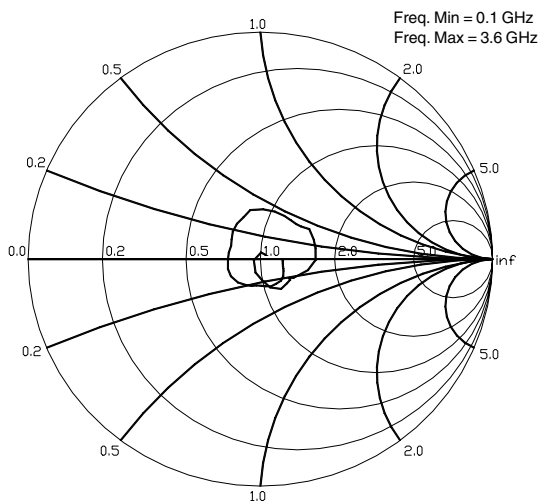
S11, Id =35mA, T=85C



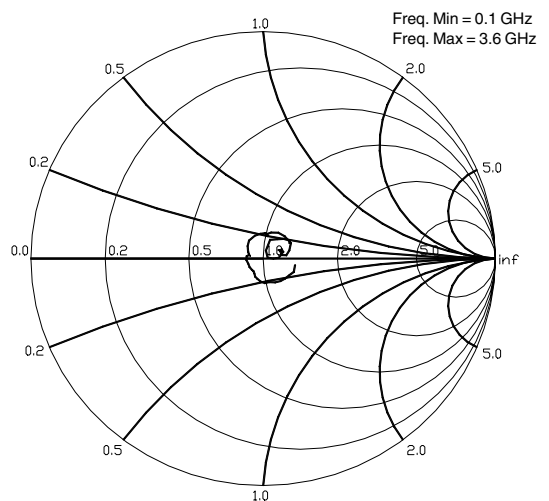
S22, Id =35mA, T=85C



S11, Id=35mA, Ta= 85C



S22, Id=35mA, Ta= 85C



Absolute Maximum Ratings

Parameter	Value	Unit
Supply Current	70	mA
Operating Temperature	-40 to +85	C
Maximum Input Power	+10	dBm
Storage Temperature Range	-40 to +85	C
Operating Junction Temperature	+150	C

Caution:



Operation of this device above any one of these parameters may cause permanent damage. Appropriate precautions in handling, packaging and testing devices must be observed.

Thermal Resistance (Lead-Junction):

97° C/W

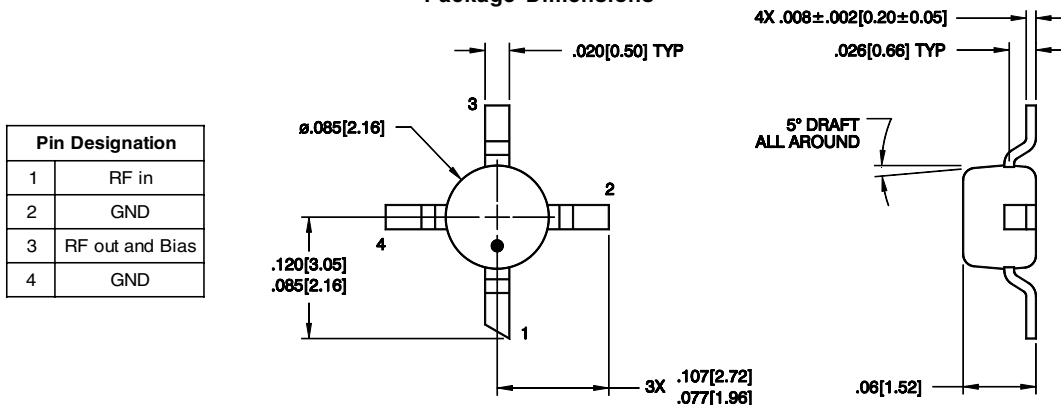
Part Number Ordering Information

Part Number	Reel Size	Devices/Reel
SGA-3286-TR1	7"	1000
SGA-3286-TR2	13"	3000

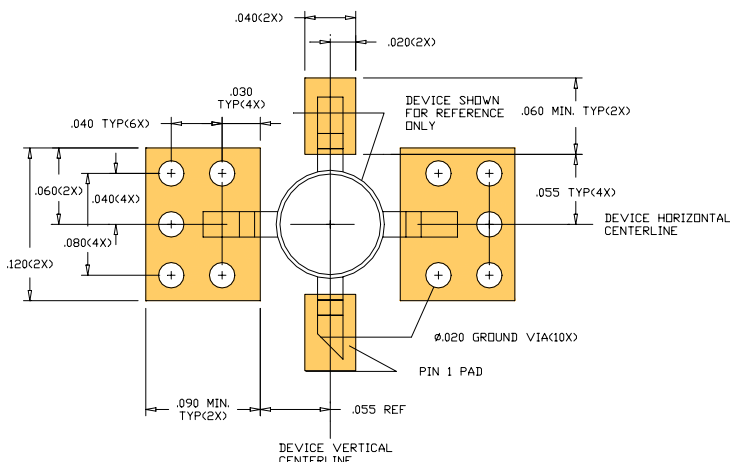
Recommended Bias Resistor Values

Supply Voltage(Vs)	4V	5V	7.5V	9V	12V
Rbias (Ohms)	37	66	137	180	266

Package Dimensions



PCB Pad Layout



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